Go to Home Page

Phenitec
For Further Growth Together
フェニテックセミコンダクター株式会社

RAPxxxS

Transient Voltage Suppressor

Features

- Anode-Common Structure(Dual TVS)
- Suitable to small packages (SOT-23) Chip Size=0.94*0.63mm
- High ESD protection level
  IEC61000-4-2(ESD) +/-30kV(Air) +/-30kV(Contact)

Applications

- Computers and Peripherals
- Communication systems
- Audio and video equipment
- Parallel ports

Item	Characteristics
Wafer Size	5inch
Chip Size	940*630um

Maximum Ratings (Ta=25degC)

Symbol	Parameter	Value	Units
Ppk	Peak Power Dissipation @8/20us(*1)	300	W
Ipp	Maximum Peak Pulse Current @8/20us(*1)	18.5	A
Tstg	Storage Temperature Range	-55 to+150	Deg C
Tj	Maximum junction temperature (*1)	150	Deg C
Vpp	Electrostatic discharge IEC61000-4-2 air discharge (*1) IEC61000-4-2 contact discharge (*1)	 ±30 ±30	 kV kV

(*1) Rating value for reference on a SOT-23 package configuration (front: Au wire 35um, back: Au eutectic), mounted on PCB of 1.5cm by 2.5cm.

Go to Home Page

Electrical Characteristics (Ta=25degC)

Device	VRWM (V)	IR (uA) @VRWM		VBR (V) @IT			IT (mA)	Vc(*1) (V) @Ipp @tp=8/20us	C (pF) @0V @1MHz	
	Max	Typ	Max	Min	Ctr	Max		Max	Typ	Max
RAP5V3S(*2)	3	-	2	5.3	5.6	5.9	1.0	16.2	170	
RAP6V1S	5.25	2.50	20	6.10	6.65	7.20	1.0	16.2	170	-
RAP6V4S	5.20	0.15	1	6.40	6.80	7.20	5.0	16.2	170	200

(*1)Package=SOT-23 (front: Au wire 35um, back: Au eutectic)

(*2) UNDER DEVELOPMENT